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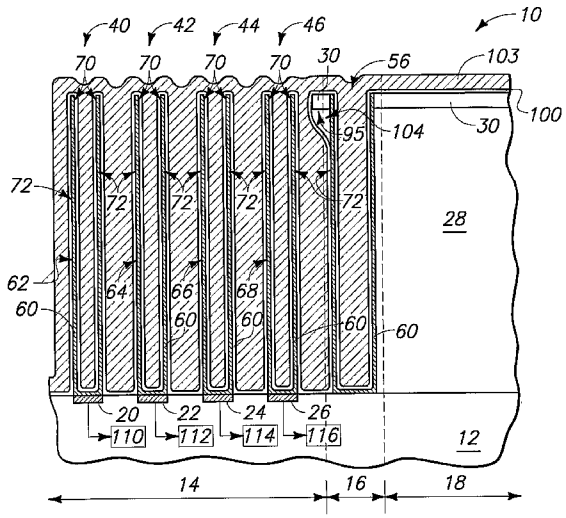
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(54) Title: CONTAINING CAPACITORS AND METHOD OF FORMING



(57) Abstract: The invention includes semiconductor constructions, and also includes methods of forming pluralities of capacitor devices. An exemplary method of the invention includes forming conductive storage node material (60) within openings in an insulative material (28) to form conductive containers. A retaining structure lattice (30) is formed in physical contact with at least some of the containers, and subsequently the insulative material (28) is removed to expose outer surfaces of the containers. The retaining structure (30) can alleviate toppling or other loss of structural integrity of the container structures. The electrically conductive containers correspond to first capacitor electrodes. After the outer sidewalls of the containers are exposed, dielectric material (100) is formed within the containers and along the exposed outer sidewalls. Subsequently, a second capacitor electrode (103) is formed over the dielectric material. The first and second capacitor electrodes, together with the dielectric material, form a plurality of capacitor devices.

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